

# CPC COOPERATIVE PATENT CLASSIFICATION

## H ELECTRICITY

(NOTE omitted)

### H10 SEMICONDUCTOR DEVICES; ELECTRIC SOLID-STATE DEVICES NOT OTHERWISE PROVIDED FOR

#### H10N ELECTRIC SOLID-STATE DEVICES NOT OTHERWISE PROVIDED FOR

##### Thermoelectric or thermomagnetic devices

- 10/00** Thermoelectric devices comprising a junction of dissimilar materials, i.e. devices exhibiting Seebeck or Peltier effects (integrated devices or assemblies of multiple devices [H10N 19/00](#))
- 10/01 . Manufacture or treatment
- 10/10 . operating with only the Peltier or Seebeck effects
- 10/13 . . characterised by the heat-exchanging means at the junction
- 10/17 . . characterised by the structure or configuration of the cell or thermocouple forming the device
- 10/80 . Constructional details
- 10/81 . . Structural details of the junction
- 10/813 . . . the junction being separable, e.g. using a spring
- 10/817 . . . the junction being non-separable, e.g. being cemented, sintered or soldered
- 10/82 . . Connection of interconnections
- 10/85 . . Thermoelectric active materials
- 10/851 . . . comprising inorganic compositions
- 10/852 . . . . comprising tellurium, selenium or sulfur
- 10/853 . . . . comprising arsenic, antimony or bismuth ([H10N 10/852](#) takes precedence)
- 10/854 . . . . comprising only metals ([H10N 10/852](#), [H10N 10/853](#) take precedence)
- 10/855 . . . . comprising compounds containing boron, carbon, oxygen or nitrogen

##### WARNING

Group [H10N 10/855](#) is impacted by reclassification into group [H10N 10/8556](#). Groups [H10N 10/855](#) and [H10N 10/8556](#) should be considered in order to perform a complete search.

- 10/8552 . . . . {the compounds being superconducting}
- 10/8556 . . . . {comprising compounds containing germanium or silicon}

##### WARNING

Group [H10N 10/8556](#) is incomplete pending reclassification of documents from group [H10N 10/855](#). Groups [H10N 10/855](#) and [H10N 10/8556](#) should be considered in order to perform a complete search.

- 10/856 . . . comprising organic compositions
- 10/857 . . . comprising compositions changing continuously or discontinuously inside the material

- 15/00** Thermoelectric devices without a junction of dissimilar materials; Thermomagnetic devices, e.g. using the Nernst-Ettingshausen effect (integrated devices or assemblies of multiple devices [H10N 19/00](#))
- 15/10 . Thermoelectric devices using thermal change of the dielectric constant, e.g. working above and below the Curie point
- 15/15 . . {Selection of materials}
- 15/20 . Thermomagnetic devices using thermal change of the magnetic permeability, e.g. working above and below the Curie point
- 19/00** Integrated devices, or assemblies of multiple devices, comprising at least one thermoelectric or thermomagnetic element covered by groups [H10N 10/00](#) - [H10N 15/00](#)
- WARNING
- Group [H10N 19/00](#) is incomplete pending reclassification of documents from groups [H01L 25/16](#), [H01L 25/162](#), [H01L 25/165](#), [H01L 25/167](#) and [H01L 25/18](#).
- All groups listed in this Warning should be considered in order to perform a complete search.
- 19/101 . {Multiple thermocouples connected in a cascade arrangement}

##### Piezoelectric, electrostrictive or magnetostrictive devices

- 30/00** Piezoelectric or electrostrictive devices (integrated devices or assemblies of multiple devices [H10N 39/00](#))
- WARNING
- Group [H10N 30/00](#) is impacted by reclassification into group [H10N 35/00](#). Groups [H10N 30/00](#) and [H10N 35/00](#) should be considered in order to perform a complete search.
- 30/01 . Manufacture or treatment
- 30/02 . . Forming enclosures or casings
- 30/03 . . Assembling devices that include piezoelectric or electrostrictive parts
- 30/04 . . Treatments to modify a piezoelectric or electrostrictive property, e.g. polarisation characteristics, vibration characteristics or mode tuning
- 30/045 . . . by polarising
- 30/05 . . Manufacture of multilayered piezoelectric or electrostrictive devices, or parts thereof, e.g. by stacking piezoelectric bodies and electrodes

- 30/053 . . . by integrally sintering piezoelectric or electrostrictive bodies and electrodes
  - 30/057 . . . by stacking bulk piezoelectric or electrostrictive bodies and electrodes
  - 30/06 . . Forming electrodes or interconnections, e.g. leads or terminals
  - 30/063 . . . Forming interconnections, e.g. connection electrodes of multilayered piezoelectric or electrostrictive parts
  - 30/067 . . . Forming single-layered electrodes of multilayered piezoelectric or electrostrictive parts
  - 30/07 . . Forming of piezoelectric or electrostrictive parts or bodies on an electrical element or another base
  - 30/071 . . . Mounting of piezoelectric or electrostrictive parts together with semiconductor elements, or other circuit elements, on a common substrate
  - 30/072 . . . by laminating or bonding of piezoelectric or electrostrictive bodies
  - 30/073 . . . . by fusion of metals or by adhesives
  - 30/074 . . . by depositing piezoelectric or electrostrictive layers, e.g. aerosol or screen printing
  - 30/076 . . . . by vapour phase deposition
  - 30/077 . . . . by liquid phase deposition
  - 30/078 . . . . by sol-gel deposition
  - 30/079 . . . . using intermediate layers, e.g. for growth control
  - 30/08 . . Shaping or machining of piezoelectric or electrostrictive bodies
  - 30/081 . . . by coating or depositing using masks, e.g. lift-off
  - 30/082 . . . by etching, e.g. lithography
  - 30/084 . . . by moulding or extrusion
  - 30/085 . . . by machining
  - 30/086 . . . . by polishing or grinding
  - 30/088 . . . . by cutting or dicing
  - 30/089 . . . . by punching
  - 30/09 . . Forming piezoelectric or electrostrictive materials
  - 30/092 . . . Forming composite materials
  - 30/093 . . . Forming inorganic materials
  - 30/095 . . . . by melting
  - 30/097 . . . . by sintering
  - 30/098 . . . Forming organic materials
  - 30/1051 . {based on piezoelectric or electrostrictive films or coatings}
  - 30/10513 . . {characterised by the underlying bases, e.g. substrates}
  - 30/10516 . . . {Intermediate layers, e.g. barrier, adhesion or growth control buffer layers}
  - 30/1061 . {based on piezoelectric or electrostrictive fibres}
  - 30/1071 . {with electrical and mechanical input and output, e.g. having combined actuator and sensor parts}
  - 30/20 . with electrical input and mechanical output, e.g. functioning as actuators or vibrators
  - 30/202 . . {using longitudinal or thickness displacement combined with bending, shear or torsion displacement}
  - 30/2023 . . . {having polygonal or rectangular shape}
  - 30/2027 . . . {having cylindrical or annular shape}
  - 30/204 . . {using bending displacement, e.g. unimorph, bimorph or multimorph cantilever or membrane benders}
  - 30/2041 . . . {Beam type}
  - 30/2042 . . . . {Cantilevers, i.e. having one fixed end}
  - 30/2043 . . . . . {connected at their free ends, e.g. parallelogram type}
  - 30/2044 . . . . . {having multiple segments mechanically connected in series, e.g. zig-zag type}
  - 30/2045 . . . . . {adapted for in-plane bending displacement}
  - 30/2046 . . . . . {adapted for multi-directional bending displacement}
  - 30/2047 . . . {Membrane type}
  - 30/2048 . . . . {having non-planar shape}
  - 30/206 . . {using only longitudinal or thickness displacement, e.g.  $d_{33}$  or  $d_{31}$  type devices}
  - 30/208 . . {using shear or torsion displacement, e.g.  $d_{15}$  type devices}
  - 30/30 . with mechanical input and electrical output, e.g. functioning as generators or sensors
  - 30/302 . . {Sensors}
  - 30/304 . . {Beam type}
  - 30/306 . . . {Cantilevers}
  - 30/308 . . {Membrane type}
  - 30/40 . with electrical input and electrical output, e.g. functioning as transformers
  - 30/50 . having a stacked or multilayer structure
  - 30/501 . . {with non-rectangular cross-section in stacking direction, e.g. polygonal, trapezoidal}
  - 30/503 . . {with non-rectangular cross-section orthogonal to the stacking direction, e.g. polygonal, circular}
  - 30/505 . . . {Annular cross-section}
  - 30/506 . . {of cylindrical shape with stacking in radial direction, e.g. coaxial or spiral type rolls}
  - 30/508 . . {adapted for alleviating internal stress, e.g. cracking control layers}
  - 30/60 . having a coaxial cable structure
  - 30/80 . Constructional details
- WARNING**
- Group [H10N 30/80](#) is impacted by reclassification into group [H10N 35/80](#).
- Groups [H10N 30/80](#) and [H10N 35/80](#) should be considered in order to perform a complete search.
- 30/802 . . {Drive or control circuitry or methods for piezoelectric or electrostrictive devices not otherwise provided for}
  - 30/804 . . . {for piezoelectric transformers (conversion of DC or AC power [H02M](#); for operating discharge lamps [H05B 41/282](#))}
  - 30/85 . . Piezoelectric or electrostrictive active materials
- WARNING**
- Group [H10N 30/85](#) is impacted by reclassification into group [H10N 35/85](#).
- Groups [H10N 30/85](#) and [H10N 35/85](#) should be considered in order to perform a complete search.
- 30/852 . . . {Composite materials, e.g. having 1-3 or 2-2 type connectivity}
  - 30/853 . . . Ceramic compositions
  - 30/8536 . . . . {Alkaline earth metal based oxides, e.g. barium titanates}
  - 30/8542 . . . . {Alkali metal based oxides, e.g. lithium, sodium or potassium niobates}

- 30/8548 . . . . {Lead based oxides}
- 30/8554 . . . . . {Lead zirconium titanate based}
- 30/8561 . . . . {Bismuth based oxides}
- 30/857 . . . Macromolecular compositions
- 30/87 . . Electrodes or interconnections, e.g. leads or terminals
- 30/871 . . . {Single-layered electrodes of multilayer piezoelectric or electrostrictive devices, e.g. internal electrodes}
- 30/872 . . . {Connection electrodes of multilayer piezoelectric or electrostrictive devices, e.g. external electrodes}
- 30/874 . . . . {embedded within piezoelectric or electrostrictive material, e.g. via connections}
- 30/875 . . . {Further connection or lead arrangements, e.g. flexible wiring boards, terminal pins}
- 30/877 . . . {Conductive materials (in general H01B 1/00)}
- 30/878 . . . . {the principal material being non-metallic, e.g. oxide or carbon based}
- 30/88 . . Mounts; Supports; Enclosures; Casings
- 30/883 . . . {Further insulation means against electrical, physical or chemical damage, e.g. protective coatings}
- 30/886 . . . {Mechanical prestressing means, e.g. springs (springs in general F16F 1/00)}

**35/00** **Magnetostrictive devices** (integrated devices or assemblies of multiple devices [H10N 39/00](#))

**WARNING**

Group [H10N 35/00](#) is incomplete pending reclassification of documents from group [H10N 30/00](#).  
Groups [H10N 30/00](#) and [H10N 35/00](#) should be considered in order to perform a complete search.

- 35/01 . Manufacture or treatment
- 35/101 . {with mechanical input and electrical output, e.g. generators, sensors}
- 35/80 . Constructional details

**WARNING**

Group [H10N 35/80](#) is incomplete pending reclassification of documents from group [H10N 30/80](#).  
Groups [H10N 30/80](#) and [H10N 35/80](#) should be considered in order to perform a complete search.

- 35/85 . . Magnetostrictive active materials

**WARNING**

Group [H10N 35/85](#) is incomplete pending reclassification of documents from group [H10N 30/85](#).  
Groups [H10N 30/85](#) and [H10N 35/85](#) should be considered in order to perform a complete search.

**39/00**

**Integrated devices, or assemblies of multiple devices, comprising at least one piezoelectric, electrostrictive or magnetostrictive element covered by groups [H10N 30/00](#) – [H10N 35/00](#)**

**WARNING**

Group [H10N 39/00](#) is incomplete pending reclassification of documents from groups [H01L 25/16](#), [H01L 25/162](#), [H01L 25/165](#), [H01L 25/167](#) and [H01L 25/18](#).

All groups listed in this Warning should be considered in order to perform a complete search.

**Galvanomagnetic or similar magnetic-effect devices**

**50/00**

**Galvanomagnetic devices** (Hall-effect devices [H10N 52/00](#); integrated devices or assemblies of multiple devices [H10N 59/00](#))

**WARNING**

Group [H10N 50/00](#) is impacted by reclassification into group [H10N 50/20](#).

Groups [H10N 50/00](#) and [H10N 50/20](#) should be considered in order to perform a complete search.

- 50/01
- 50/10
- 50/20

- . Manufacture or treatment
- . Magnetoresistive devices
- . Spin-polarised current-controlled devices (magnetoresistive devices [H10N 50/10](#))

**WARNING**

Group [H10N 50/20](#) is incomplete pending reclassification of documents from group [H10N 50/00](#).

Groups [H10N 50/00](#) and [H10N 50/20](#) should be considered in order to perform a complete search.

- 50/80
- 50/85

- . Constructional details
- . . Magnetic active materials

**WARNING**

Group [H10N 50/85](#) is impacted by reclassification into group [H10N 52/85](#).

Groups [H10N 50/85](#) and [H10N 52/85](#) should be considered in order to perform a complete search.

**52/00**

**Hall-effect devices** (integrated devices or assemblies of multiple devices [H10N 59/00](#))

- 52/01
- 52/101
- 52/80
- 52/85

- . Manufacture or treatment
- . {Semiconductor Hall-effect devices}
- . Constructional details
- . . Magnetic active materials

**WARNING**

Group [H10N 52/85](#) is incomplete pending reclassification of documents from group [H10N 50/85](#).

Groups [H10N 50/85](#) and [H10N 52/85](#) should be considered in order to perform a complete search.

**59/00** **Integrated devices, or assemblies of multiple devices, comprising at least one galvanomagnetic or Hall-effect element covered by groups [H10N 50/00](#) - [H10N 52/00](#) (MRAM devices [H10B 61/00](#))**

**WARNING**

Group [H10N 59/00](#) is incomplete pending reclassification of documents from groups [H01L 25/16](#), [H01L 25/162](#), [H01L 25/165](#), [H01L 25/167](#) and [H01L 25/18](#).

Group [H10N 59/00](#) is also impacted by reclassification into group [H10B 61/00](#).

All groups listed in this Warning should be considered in order to perform a complete search.

**Superconducting devices**

**60/00** **Superconducting devices (integrated devices or assemblies of multiple devices [H10N 69/00](#))**

60/01 . Manufacture or treatment

60/0128 . . {of composite superconductor filaments (comprising copper oxide [H10N 60/0268](#))}

60/0156 . . {of devices comprising Nb or an alloy of Nb with one or more of the elements of group 4, e.g. Ti, Zr, Hf}

60/0184 . . {of devices comprising intermetallic compounds of type A-15, e.g. Nb<sub>3</sub>Sn}

60/0212 . . {of devices comprising molybdenum chalcogenides}

60/0241 . . {of devices comprising nitrides or carbonitrides}

60/0268 . . {of devices comprising copper oxide}

60/0296 . . . {Processes for depositing or forming superconductor layers}

60/0324 . . . . {from a solution}

60/0352 . . . . {from a suspension or slurry, e.g. screen printing; doctor blade casting}

60/0381 . . . . {by evaporation independent of heat source, e.g. MBE}

60/0408 . . . . {by sputtering}

60/0436 . . . . {by chemical vapour deposition [CVD]}

60/0464 . . . . {by metalloorganic chemical vapour deposition [MOCVD]}

60/0492 . . . . {by thermal spraying, e.g. plasma deposition}

60/0521 . . . . {by pulsed laser deposition, e.g. laser sputtering; laser ablation}

60/0548 . . . . {by precursor deposition followed by after-treatment, e.g. oxidation}

60/0576 . . . . {characterised by the substrate}

60/0604 . . . . . {Monocrystalline substrates, e.g. epitaxial growth}

60/0632 . . . . . {Intermediate layers, e.g. for growth control}

60/0661 . . . {After-treatment, e.g. patterning}

60/0688 . . . . {Etching}

60/0716 . . . . {Passivation}

60/0744 . . . {Manufacture or deposition of contacts or electrodes}

60/0772 . . . {Processes including the use of precursors}

60/0801 . . . {Processes peculiar to the manufacture or treatment of filaments or composite wires}

60/0828 . . . {Introducing flux pinning centres}

60/0856 . . {of devices comprising metal borides, e.g. MgB<sub>2</sub>}

60/0884 . . {Treatment of superconductor layers by irradiation, e.g. ion-beam, electron-beam, laser beam, X-rays (irradiation devices [G21K](#), [H01J](#))}

60/0912 . . {of Josephson-effect devices}

60/0941 . . . {comprising high-T<sub>c</sub> ceramic materials}

60/10 . Junction-based devices

60/11 . . {Single electron tunnelling devices}

60/12 . . Josephson-effect devices

60/124 . . . {comprising high-T<sub>c</sub> ceramic materials}

60/126 . . . {comprising metal borides, e.g. MgB<sub>2</sub>}

60/128 . . {having three or more electrodes, e.g. transistor-like structures}

60/20 . Permanent superconducting devices

60/202 . . {comprising metal borides, e.g. MgB<sub>2</sub>}

60/203 . . {comprising high-T<sub>c</sub> ceramic materials}

60/205 . . {having three or more electrodes, e.g. transistor-like structures ([H10N 60/128](#) takes precedence)}

60/207 . . . {Field effect devices}

60/208 . . {based on Abrikosov vortices}

60/30 . Devices switchable between superconducting and normal states

60/35 . Cryotrons

60/355 . . . Power cryotrons

60/80 . Constructional details

60/805 . . {for Josephson-effect devices}

60/81 . . Containers; Mountings

60/815 . . . {for Josephson-effect devices}

60/82 . . Current path

60/83 . . Element shape

60/84 . . Switching means for devices switchable between superconducting and normal states

60/85 . . Superconducting active materials

60/851 . . . {Organic materials}

60/853 . . . . {Fullerene superconductors, e.g. soccerball-shaped allotrope of carbon, e.g. C<sub>60</sub>, C<sub>94</sub> (fullerenes in general [C07C 13/00](#))}

60/855 . . . {Ceramic materials}

60/857 . . . . {comprising copper oxide}

60/858 . . . . . {Multi-layered structures, e.g. superlattices}

60/99 . {Alleged superconductivity}

**69/00** **Integrated devices, or assemblies of multiple devices, comprising at least one superconducting element covered by group [H10N 60/00](#)**

**WARNING**

Group [H10N 69/00](#) is incomplete pending reclassification of documents from groups [H01L 25/16](#), [H01L 25/162](#), [H01L 25/165](#), [H01L 25/167](#) and [H01L 25/18](#).

All groups listed in this Warning should be considered in order to perform a complete search.

**Other electric solid-state devices**

**70/00** **Solid-state devices without a potential-jump barrier or surface barrier, and specially adapted for rectifying, amplifying, oscillating or switching (integrated devices or assemblies of multiple devices [H10N 79/00](#))**

70/011 . {Manufacture or treatment of multistable switching devices}



- 70/021 . . {Formation of the switching material, e.g. layer deposition}
- 70/023 . . . {by chemical vapor deposition, e.g. MOCVD, ALD}
- 70/026 . . . {by physical vapor deposition, e.g. sputtering}
- 70/028 . . . {by conversion of electrode material, e.g. oxidation}
- 70/041 . . {Modification of the switching material, e.g. post-treatment, doping}
- 70/043 . . . {by implantation}
- 70/046 . . . {by diffusion, e.g. photo-dissolution}
- 70/061 . . {Patterning of the switching material}
- 70/063 . . . {by etching of pre-deposited switching material layers, e.g. lithography}
- 70/066 . . . {by filling of openings, e.g. damascene method}
- 70/068 . . . {by processes specially adapted for achieving sub-lithographic dimensions, e.g. using spacers}
- 70/10 . Solid-state travelling-wave devices
- 70/151 . {Charge density wave transport devices}
- 70/20 . Multistable switching devices, e.g. memristors
- 70/231 . . {based on solid-state phase change, e.g. between amorphous and crystalline phases, Ovshinsky effect}
- 70/235 . . . {between different crystalline phases, e.g. cubic and hexagonal}
- 70/24 . . {based on migration or redistribution of ionic species, e.g. anions, vacancies}
- 70/245 . . . {the species being metal cations, e.g. programmable metallization cells}
- 70/25 . . {based on bulk electronic defects, e.g. trapping of electrons}
- 70/253 . . {having three or more terminals, e.g. transistor-like devices}
- 70/257 . . {based on radiation or particle beam assisted switching, e.g. optically controlled devices}
- 70/801 . {Constructional details of multistable switching devices}
- 70/821 . . {Device geometry}
- 70/823 . . . {adapted for essentially horizontal current flow, e.g. bridge type devices}
- 70/826 . . . {adapted for essentially vertical current flow, e.g. sandwich or pillar type devices}
- 70/8265 . . . . {on sidewalls of dielectric structures, e.g. mesa or cup type devices}
- 70/828 . . . {Current flow limiting means within the switching material region, e.g. constrictions}
- 70/841 . . {Electrodes}
- 70/8413 . . . {adapted for resistive heating}
- 70/8416 . . . {adapted for supplying ionic species}
- 70/8418 . . . {adapted for focusing electric field or current, e.g. tip-shaped}
- 70/861 . . {Thermal details}
- 70/8613 . . . {Heating or cooling means other than resistive heating electrodes, e.g. heater in parallel}
- 70/8616 . . . {Thermal insulation means}
- 70/881 . . {Switching materials}
- 70/882 . . . {Compounds of sulfur, selenium or tellurium, e.g. chalcogenides}
- 70/8822 . . . . {Sulfides, e.g. CuS}
- 70/8825 . . . . {Selenides, e.g. GeSe}
- 70/8828 . . . . {Tellurides, e.g. GeSbTe}

- 70/883 . . . {Oxides or nitrides}
- 70/8833 . . . . {Binary metal oxides, e.g. TaO<sub>x</sub>}
- 70/8836 . . . . {Complex metal oxides, e.g. perovskites, spinels}
- 70/884 . . . {Other compounds of groups 13-15, e.g. elemental or compound semiconductors}
- 70/8845 . . . . {Carbon or carbides}

**79/00 Integrated devices, or assemblies of multiple devices, comprising at least one solid-state element covered by group [H10N 70/00](#) (ReRAM devices [H10B 63/00](#); PCRAM devices [H10B 63/10](#))**

#### **WARNING**

Group [H10N 79/00](#) is incomplete pending reclassification of documents from groups [H01L 25/16](#), [H01L 25/162](#), [H01L 25/165](#), [H01L 25/167](#), [H01L 25/18](#) and [H10B 63/00](#).

All groups listed in this Warning should be considered in order to perform a complete search.

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**80/00 Bulk negative-resistance effect devices (integrated devices or assemblies of multiple devices [H10N 89/00](#))**

- 80/01 . {Manufacture or treatment}
- 80/10 . Gunn-effect devices
- 80/103 . . {controlled by electromagnetic radiation}
- 80/107 . . {Gunn diodes}

**89/00 Integrated devices, or assemblies of multiple devices, comprising at least one bulk negative resistance effect element covered by group [H10N 80/00](#)**

#### **WARNING**

Group [H10N 89/00](#) is incomplete pending reclassification of documents from groups [H01L 25/16](#), [H01L 25/162](#), [H01L 25/165](#), [H01L 25/167](#) and [H01L 25/18](#).

All groups listed in this Warning should be considered in order to perform a complete search.

- 89/02 . {Gunn-effect devices}

**97/00 Electric solid-state thin-film or thick-film devices, not otherwise provided for**

**99/00 Subject matter not provided for in other groups of this subclass**

- 99/03 . {Devices using Mott metal-insulator transition, e.g. field effect transistors}
- 99/05 . {Quantum devices, e.g. quantum interference devices, metal single electron transistors}